

OVERVIEW

The SM5010 series are crystal oscillator module ICs. They incorporate oscillator and output buffer circuits, employing built-in oscillator capacitors and feedback resistors with excellent frequency response, eliminating the need for external components to form a stable crystal oscillator. There are 7 oscillator configurations available for design and application optimization.

FEATURES

- 7 types of oscillation circuit structure
 - For fundamental oscillator**
 - 5010A××: Simple structure with low frequency variation
 - 5010B××: Low crystal current type with R_D built-in oscillation circuit
 - 5010CL×: Oscillation stop function built-in
 - 5010DN×: External capacitors, C_G and C_D required
 - 5010EA×: Low current consumption type
 - For 3rd overtone oscillator**
 - 5010F××: Suitable for round blank
 - 5010H××: External resistor, R_f required
- 2.7 to 5.5V operating supply voltage
- Capacitors C_G , C_D built-in
- Inverter amplifier feedback resistor built-in
- Output duty level
 - TTL level: AK×, BK×, HK×
 - CMOS level: AN×, AH×, BN×, BH×, CL×, DN×, EA×, FN×, FH×, HN×
- Oscillator frequency output (f_O , $f_O/2$, $f_O/4$, $f_O/8$, $f_O/16$ determined by internal connection)
- Standby function
- Pull-up resistor built-in
- 8-pin SOP (SM5010×××S)
- Chip form (CF5010×××)

SERIES CONFIGURATION

For Fundamental Oscillator

Version ¹	Operating supply voltage range [V]	Built-in capacitance		R_D [Ω]	Output current ($V_{DD} = 5V$) [mA]	Output duty level	Output frequency	INHN input level ($V_{DD} = 5V$)	Standby mode	
		C_G [pF]	C_D [pF]						Oscillator stop function	Output state
CF5010AN1	2.7 to 5.5	29	29	-	16	CMOS	f_O	TTL	No	High impedance
CF5010AN2						$f_O/2$				
CF5010AN3						$f_O/4$				
CF5010AN4						$f_O/8$				
CF5010AK1	4.5 to 5.5	29	29	-	16	TTL	f_O	TTL	No	High impedance
CF5010AH1	2.7 to 5.5	29	29	-	4	CMOS	f_O	TTL	No	High impedance
CF5010AH2							$f_O/2$			
CF5010AH3							$f_O/4$			
CF5010AH4							$f_O/8$			
CF5010BN1	2.7 to 5.5	22	22	820	16	CMOS	f_O	TTL	No	High impedance
CF5010BN2						$f_O/2$				
CF5010BN3						$f_O/4$				
CF5010BN4						$f_O/8$				
CF5010BN5						$f_O/16$				
CF5010BK1	4.5 to 5.5	22	22	820	16	TTL	f_O	TTL	No	High impedance
CF5010BH1	2.7 to 5.5	22	22	820	4	CMOS	f_O	TTL	No	High impedance
CF5010BH2							$f_O/2$			
CF5010BH3							$f_O/4$			
CF5010BH4							$f_O/8$			
CF5010CL1	2.7 to 5.5	18	18	-	16	CMOS	f_O	CMOS	Yes	High impedance
CF5010CL2							$f_O/2$			
CF5010CL3							$f_O/4$			
CF5010CL4							$f_O/8$			
CF5010CL5							$f_O/16$			
CF5010DN1	2.7 to 5.5	-	-	820	16	CMOS	f_O	TTL	No	High impedance
CF5010EA1	2.7 to 5.5	10	15	820	4	CMOS	f_O	TTL	Yes	LOW
CF5010EA2							$f_O/2$			

1. Package devices have designation SM5010×××S.

SERIES CONFIGURATION

For 3rd Overtone Oscillator

Version	Operating supply voltage range [V]	gm ratio	Built-in capacitance		R _f [kΩ]	Output current (V _{DD} = 5V) [mA]	Output duty level
			C _G [pF]	C _D [pF]			
CF5010FNA	2.7 to 5.5	1.00	13	15	4.2	16	CMOS
CF5010FNC			11	17	3.1		
CF5010FND			13	17	2.2		
CF5010FNE	4.5 to 5.5		8	15	2.2		
CF5010FHA	4.5 to 5.5	1.00	13	15	4.2	4	CMOS
CF5010FHC			11	17	3.1		
CF5010FHD			13	17	2.2		
CF5010FHE			8	15	2.2		
CF5010HN1	4.5 to 5.5	1.17	13	17	200	16	CMOS
CF5010HK1	4.5 to 5.5	1.17	13	17	200	16	TTL

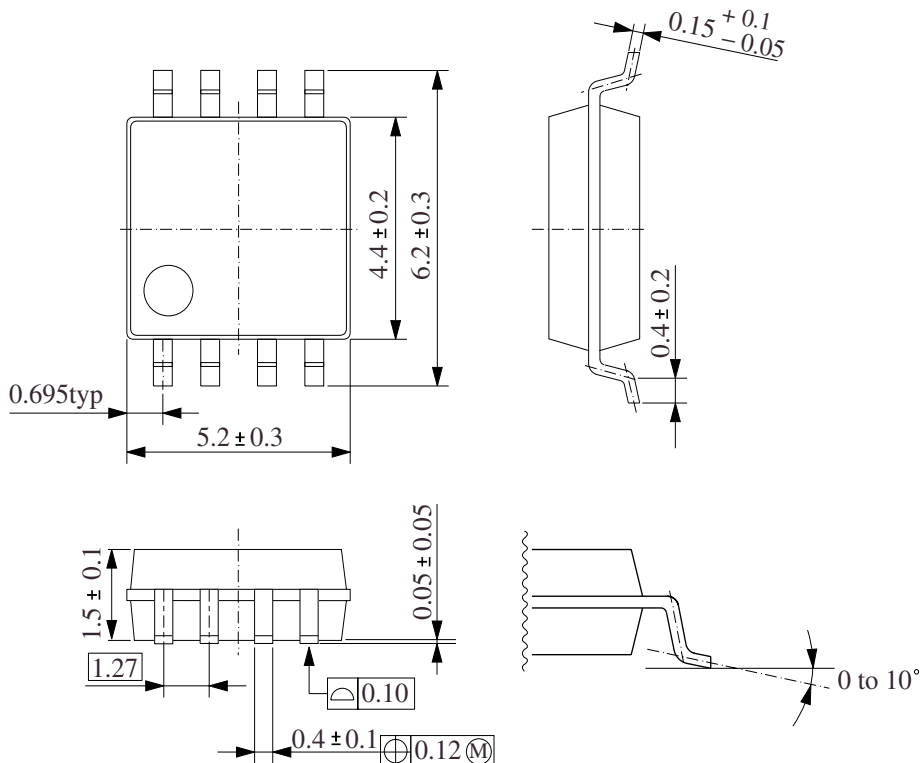
ORDERING INFORMATION

Device	Package
SM5010xxxS	8-pin SOP
CF5010xxx-1	Chip form

PACKAGE DIMENSIONS

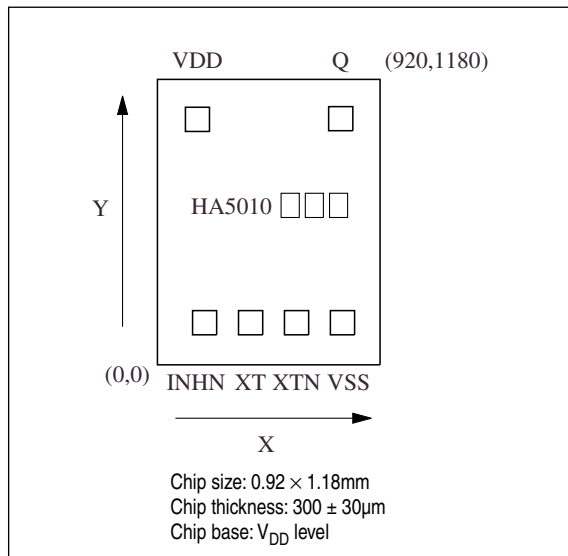
(Unit: mm)

- 8-pin SOP



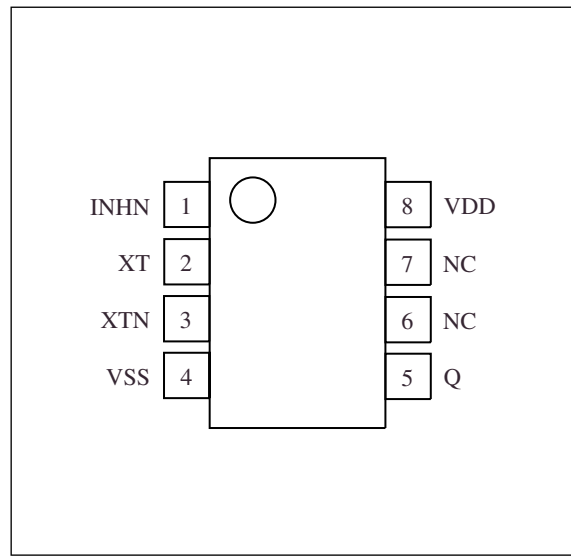
PAD LAYOUT

(Unit: μm)



PINOUT

(Top view)



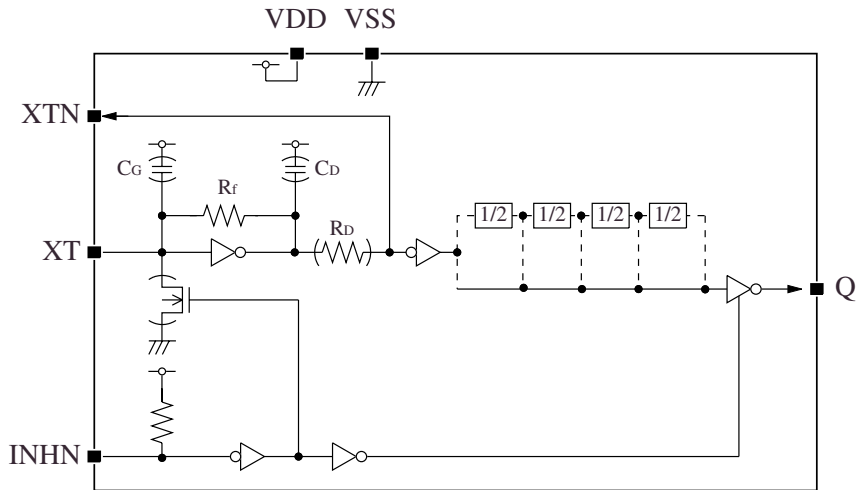
PIN DESCRIPTION and PAD DIMENSIONS

Number	Name	I/O	Description	Pad dimensions [μm]	
				X	Y
1	INHN	I	Output state control input. Standby mode when LOW, pull-up resistor built in. In the case of the 5010CLx, the oscillator stops and Power-saving pull-up resistor is built-in to reduce current consumption at standby mode.	195	174.4
2	XT	I	Amplifier input.	385	174.4
3	XTN	O	Amplifier output.	575	174.4
4	VSS	-	Ground	765	174.4
5	Q	O	Output. Output frequency (f_0 , $f_0/2$, $f_0/4$, $f_0/8$, $f_0/16$) determined by internal connection	757.6	1017.6
6	NC	-	No connection	-	-
7	NC	-	No connection	-	-
8	VDD	-	Supply voltage	165.4	1014.6

BLOCK DIAGRAM

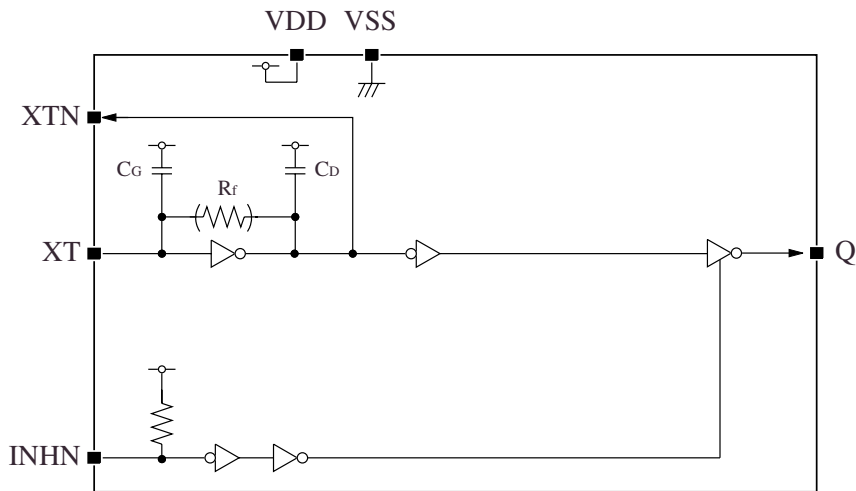
For Fundamental Oscillator

- 5010Axx, Bxx, CLx, DNx, EAx series



For 3rd Overtone Oscillator

- 5010Fxx, Hxx series



FUNCTIONAL DESCRIPTION

Standby Function

5010AH×, AK×, AN×, BH×, BK×, BN×, DN×, FN×, FH×, HN×, HK× series

When INHN goes LOW, the output on Q becomes high impedance, but internally the oscillator does not stop.

5010CL× series

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes high impedance.

5010EA× series

When INHN goes LOW, the oscillator stops and the oscillator output on Q becomes LOW.

Version	INHN	Q	Oscillator
AH×, AK×, AN×, BH×, BK×, BN×, DN×, FH×, FN×, HN×, HK× series	HIGH (or open)	Any f_O , $f_O/2$, $f_O/4$, $f_O/8$ or $f_O/16$ output frequency	Normal operation
	LOW	High impedance	Normal operation
CL× series	HIGH (or open)	Any f_O , $f_O/2$, $f_O/4$, $f_O/8$ or $f_O/16$ output frequency	Normal operation
	LOW	High impedance	Stopped
EA× series	HIGH (or open)	Either f_O or $f_O/2$ output frequency	Normal operation
	LOW	LOW	Stopped

Power-saving Pull-up Resistor (CL series only)

The INHN pull-up resistance changes in response to the input level (HIGH or LOW). When INHN goes LOW (standby state), the pull-up resistance becomes large to reduce the current consumption during standby.

SPECIFICATIONS

Absolute Maximum Ratings

 $V_{SS} = 0V$

Parameter	Symbol	Condition	Rating	Unit
Supply voltage range	V_{DD}		-0.5 to +7.0	V
Input voltage range	V_{IN}		-0.5 to $V_{DD} + 0.5$	V
Output voltage range	V_{OUT}		-0.5 to $V_{DD} + 0.5$	V
Operating temperature range	T_{opr}		-40 to +85	°C
Storage temperature range	T_{stg}	Chip form	-65 to +150	°C
		8-pin SOP	-55 to +125	
Output current	I_{OUT}	AH×, BH×, FH×, EA×	10	mA
		AN×, AK×, BN×, BK×, CL×, DN×, FN×, HN×, HK×	25	
Power dissipation	P_D	8-pin SOP	500	mW

Recommended Operating Conditions

3V operation

 $V_{SS} = 0V$

Parameter	Symbol	Version	Condition	Rating	Unit
Operating supply voltage	V_{DD}	All version		2.7 to 3.6	V
Input voltage	V_{IN}	All version		V_{SS} to V_{DD}	V
Operating temperature	T_{OPR}	5010AN×		-10 to +70	°C
		5010AH×			
		5010BN×			
		5010BH×			
		5010CL×		-20 to +80	
		5010DN1		-10 to +70	
		5010EA×			
		5010FN×			
Operating frequency	f	5010AN×	$C_L \leq 15pF$	2 to 30	MHz
		5010AH×		2 to 16	
		5010BN×		2 to 30	
		5010BH×		2 to 16	
		5010CL×		2 to 30	
		5010DN1			
		5010EA×			
		5010FN×		22 to 40	

SM5010 series

5V operation

$V_{SS} = 0V$

Parameter	Symbol	Version	Condition	Rating	Unit	
Operating supply voltage	V_{DD}	All version		4.5 to 5.5	V	
Input voltage	V_{IN}	All version		V_{SS} to V_{DD}	V	
Operating temperature	T_{OPR}	5010AN×		-40 to +85	°C	
		5010AK×				
		5010AH×				
		5010BN×				
		5010BK×				
		5010BH×				
		5010CL×				
		5010DN1				
		5010EA×	$C_L \leq 15pF, f = 2 \text{ to } 30MHz$			-10 to +70
			$C_L \leq 15pF, f = 2 \text{ to } 40MHz$			
		5010FN×	$C_L \leq 50pF, 30MHz \leq f \leq 50MHz$			-20 to +80
			$C_L \leq 15pF, 50MHz \leq f \leq 70MHz$			-15 to +75
		5010FH×	$C_L \leq 15pF, 30MHz \leq f \leq 50MHz$			-20 to +80
			$C_L \leq 15pF, 50MHz \leq f \leq 60MHz$			-15 to +75
		5010HN1				-40 to +85
5010HK1						
Operating frequency	f	5010AN×	$C_L \leq 50pF$	2 to 30	MHz	
		5010AK×	$C_L \leq 15pF$			
		5010AH×				
		5010BN×	$C_L \leq 50pF$			
		5010BK×	$C_L \leq 15pF$			
		5010BH×				
		5010CL×	$C_L \leq 50pF$			
		5010DN1				
		5010EA×	$C_L \leq 15pF, Ta = -40 \text{ to } +85^\circ C$			2 to 40
		5010FN×	$C_L \leq 50pF, Ta = -20 \text{ to } +80^\circ C$			30 to 50
			$C_L \leq 15pF, Ta = -15 \text{ to } +75^\circ C$			50 to 70
		5010FH×	$C_L \leq 15pF, Ta = -20 \text{ to } +80^\circ C$			30 to 50
			$C_L \leq 15pF, Ta = -15 \text{ to } +75^\circ C$			50 to 60
		5010HN1	$C_L \leq 50pF$			22 to 50
		5010HK1	$C_L \leq 15pF$			

SM5010 series

Electrical Characteristics

5010AN×, BN×, DN× series

3V operation: $V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 8mA$	2.1	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.5	V	
Output leakage current	I_z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 3.6V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 15pF$, $f = 30MHz$	5010×N1	–	5	10	mA
			5010×N2	–	3.5	7	
			5010×N3	–	2.5	5	
			5010×N4	–	2	4	
			5010×N5	–	2	4	
INH N pull-up resistance	R_{UP2}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value	5010B××	690	820	940	Ω
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010A××	26	29	32	pF
			5010B××	20	22	24	
	C_D		5010A××	26	29	32	
			5010B××	20	22	24	

5010AN×, AK×, BN×, BK×, DN× series

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 16mA$	3.9	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 16mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.8	V	
Output leakage current	I_z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 50pF$, $f = 30MHz$	5010×N1	–	15	30	mA
			5010×N2	–	9	18	
			5010×N3	–	6	12	
			5010×N4	–	5	10	
			5010×N5	–	5	10	
		Measurement cct 3, load cct 2, INHN = open, $C_L = 15pF$, $f = 30MHz$	5010×K1	–	10	20	
INH N pull-up resistance	R_{UP2}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value	5010B××	690	820	940	Ω
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010A××	26	29	32	pF
			5010B××	20	22	24	
	C_D		5010A××	26	29	32	
			5010B××	20	22	24	

SM5010 series

5010AH×, BH× series

3V operation: $V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 2mA$	2.1	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 2mA$	–	0.3	0.5	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.5	V	
Output leakage current	I_z	Q: Measurement cct 2, INH N = LOW, $V_{DD} = 3.6V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$, $f = 16MHz$	5010×H1	–	3	6	mA
			5010×H2	–	2	4	
			5010×H3	–	1.5	3	
			5010×H4	–	1.5	2.5	
INH N pull-up resistance	R_{UP2}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value	5010B××	690	820	940	Ω
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010A××	26	29	32	pF
			5010B××	20	22	24	
	C_D		5010A××	26	29	32	
			5010B××	20	22	24	

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 4mA$	3.9	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 4mA$	–	0.3	0.5	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.8	V	
Output leakage current	I_z	Q: Measurement cct 2, INH N = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$, $f = 30MHz$	5010×H1	–	9	18	mA
			5010×H2	–	6	12	
			5010×H3	–	5	10	
			5010×H4	–	4	8	
INH N pull-up resistance	R_{UP2}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value	5010B××	690	820	940	Ω
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010A××	26	29	32	pF
			5010B××	20	22	24	
	C_D		5010A××	26	29	32	
			5010B××	20	22	24	

SM5010 series

5010CL× series

3V operation: $V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -20$ to $+80^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 8mA$	2.2	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 3.6V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 15pF$, $f = 30MHz$	5010CL1	–	5	10	mA
			5010CL2	–	3.5	7	
			5010CL3	–	2.5	5	
			5010CL4	–	2	4	
			5010CL5	–	2	4	
Standby current	I_{ST}	Measurement cct 6, INHN = LOW	–	–	5	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	2	4	15	$M\Omega$	
	R_{UP2}		40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	16	18	20	pF	
	C_D		16	18	20		

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 16mA$	4.0	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 16mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	$0.7V_{DD}$	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	$0.3V_{DD}$	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 50pF$, $f = 30MHz$	5010CL1	–	15	30	mA
			5010CL2	–	9	18	
			5010CL3	–	6	12	
			5010CL4	–	5	10	
			5010CL5	–	5	10	
Standby current	I_{ST}	Measurement cct 6, INHN = LOW	–	–	10	μA	
INH N pull-up resistance	R_{UP1}	Measurement cct 4	1	2	8	$M\Omega$	
	R_{UP2}		40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	16	18	20	pF	
	C_D		16	18	20		

SM5010 series

5010EA× series

3V operation: $V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 2mA$	2.1	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 2mA$	–	0.3	0.5	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.5	V	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$, $f = 30MHz$	5010EA1	–	4	8	mA
			5010EA2	–	2.5	5	
INH N pull-up resistance	R_{UP2}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value	690	820	940	Ω	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	9	10	11	pF	
	C_D		13	15	17		

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 3.2mA$	3.9	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 3.2mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.8	V	
Current consumption	I_{DD1}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$, $f = 30MHz$	5010EA1	–	6	12	mA
			5010EA2	–	5	10	
	I_{DD2}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$, $f = 40MHz$	5010EA1	–	9	18	
			5010EA2	–	6	12	
INH N pull-up resistance	R_{UP2}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Oscillator amplifier output resistance	R_D	Design value	690	820	940	Ω	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	9	10	11	pF	
	C_D		13	15	17		

SM5010 series

5010FN× series

3V operation: $V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^{\circ}C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 2.7V$, $I_{OH} = 8mA$	2.2	2.4	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 2.7V$, $I_{OL} = 8mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.5	V	
Output leakage current	I_Z	Q: Measurement cct 2, INH N = LOW, $V_{DD} = 3.6V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$	5010FNA, FNC $f = 30MHz$	–	8	16	mA
			5010FND $f = 40MHz$	–	10	20	
INH N pull-up resistance	R_{UP}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	5010FNA	3.57	4.2	4.83	$k\Omega$
			5010FNC	2.63	3.1	3.57	
			5010FND	1.87	2.2	2.53	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010FNA	11.7	13	14.3	pF
			5010FNC	9.9	11	12.1	
			5010FND	11.7	13	14.3	
	C_D		5010FNA	13.5	15	16.5	
			5010FNC	15.3	17	18.7	
			5010FND	15.3	17	18.7	

SM5010 series

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$

$30 \leq f \leq 50MHz$: $T_a = -20$ to $+80^\circ C$, $50 < f \leq 70MHz$: $T_a = -15$ to $+75^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 16mA$	3.9	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 16mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.8	V	
Output leakage current	I_Z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD1}	Measurement cct 3, load cct 1, INH N = open, $C_L = 15pF$	5010FNE $f = 70MHz$	–	25	50	mA
	I_{DD2}	Measurement cct 3, load cct 1, INH N = open, $C_L = 50pF$	5010FNA, FNC $f = 40MHz$	–	23	45	
			5010FND $f = 50MHz$	–	25	50	
INH N pull-up resistance	R_{UP}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	5010FNA	3.57	4.2	4.83	$k\Omega$
			5010FNC	2.63	3.1	3.57	
			5010FND	1.87	2.2	2.53	
			5010FNE	1.87	2.2	2.53	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010FNA	11.7	13	14.3	pF
			5010FNC	9.9	11	12.1	
			5010FND	11.7	13	14.3	
			5010FNE	7.2	8	8.8	
	C_D		5010FNA	13.5	15	16.5	
			5010FNC	15.3	17	18.7	
			5010FND	15.3	17	18.7	
			5010FNE	13.5	15	16.5	

SM5010 series

5010FH× series

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$

$30 \leq f \leq 50MHz$: $T_a = -20$ to $+80^\circ C$, $50 < f \leq 60MHz$: $T_a = -15$ to $+75^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 4mA$	3.9	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 4mA$	–	0.3	0.5	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.8	V	
Output leakage current	I_z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD}	Measurement cct 3, load cct 1, INHN = open, $C_L = 15pF$	5010FHA, FHC $f = 40MHz$	–	13	26	mA
			5010FHD $f = 50MHz$	–	15	30	
			5010FHE $f = 60MHz$	–	17	34	
INH N pull-up resistance	R_{UP}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	5010FHA	3.57	4.2	4.83	$k\Omega$
			5010FHC	2.63	3.1	3.57	
			5010FHD	1.87	2.2	2.53	
			5010FHE	1.87	2.2	2.53	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	5010FHA	11.7	13	14.3	pF
			5010FHC	9.9	11	12.1	
			5010FHD	11.7	13	14.3	
			5010FHE	7.2	8	8.8	
	C_D		5010FHA	13.5	15	16.5	
			5010FHC	15.3	17	18.7	
			5010FHD	15.3	17	18.7	
			5010FHE	13.5	15	16.5	

5010HN×, HK× series

5V operation: $V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
HIGH-level output voltage	V_{OH}	Q: Measurement cct 1, $V_{DD} = 4.5V$, $I_{OH} = 16mA$	3.9	4.2	–	V	
LOW-level output voltage	V_{OL}	Q: Measurement cct 2, $V_{DD} = 4.5V$, $I_{OL} = 16mA$	–	0.3	0.4	V	
HIGH-level input voltage	V_{IH}	INH N	2.0	–	–	V	
LOW-level input voltage	V_{IL}	INH N	–	–	0.8	V	
Output leakage current	I_z	Q: Measurement cct 2, INHN = LOW, $V_{DD} = 5.5V$	$V_{OH} = V_{DD}$	–	–	10	μA
			$V_{OL} = V_{SS}$	–	–	10	
Current consumption	I_{DD1}	Measurement cct 3, load cct 2, INHN = open, $C_L = 15pF$, $f = 50MHz$	5010HK1	–	20	40	mA
	I_{DD2}	Measurement cct 3, load cct 1, INHN = open, $C_L = 50pF$, $f = 50MHz$	5010HN1	–	25	50	
INH N pull-up resistance	R_{UP}	Measurement cct 4	40	100	250	$k\Omega$	
Feedback resistance	R_f	Measurement cct 5	80	200	500	$k\Omega$	
Built-in capacitance	C_G	Design value. A monitor pattern on a wafer is tested.	11.7	13	14.3	pF	
	C_D		15.3	17	18.7		

Switching Characteristics

5010AN×, BN×, DN× series

3V operation/Duty level: CMOS

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.1V_{DD}$ to $0.9V_{DD}$	–	3.0	6.0	ns
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.9V_{DD}$ to $0.1V_{DD}$	–	3.0	6.0	ns
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 30MHz$	40	–	60	%
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns
Output enable delay time	t_{PZL}		–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

5010AN×, AK×, BN×, BK×, DN× series

5V operation/Duty level: CMOS (5010AN×, BN×, DN1)

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	2.0	4.0	ns
	t_{r2}		$C_L = 50pF$	–	4.0	8.0	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	2.0	4.0	ns
	t_{f2}		$C_L = 50pF$	–	4.0	8.0	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 50pF$, $f = 30MHz$	45	–	55	%	
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

5V operation/Duty level: TTL (5010×K1, AN2, AN3, AN4, BN2, BN3, BN4, BN5)

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Output rise time	t_{r3}	Measurement cct 6, load cct 2, $C_L = 15pF$, $0.4V$ to $2.4V$	–	1.5	3.0	ns
Output fall time	t_{f3}	Measurement cct 6, load cct 2, $C_L = 15pF$, $2.4V$ to $0.4V$	–	1.5	3.0	ns
Output duty cycle ¹	Duty	Measurement cct 6, load cct 2, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 30MHz$	45	–	55	%
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 2, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns
Output enable delay time	t_{PZL}		–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

SM5010 series

5010AH×, BH× series

3V operation/Duty level: CMOS

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.1V_{DD}$ to $0.9V_{DD}$	–	8	16	ns
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.9V_{DD}$ to $0.1V_{DD}$	–	8	16	ns
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 16MHz$	40	–	60	%
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns
Output enable delay time	t_{PZL}		–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

5V operation/Duty level: CMOS

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	5	10	ns
	t_{r2}		$C_L = 50pF$	–	13	26	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	5	10	ns
	t_{f2}		$C_L = 50pF$	–	13	26	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 30MHz$	45	–	55	%	
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

5010CL× series**3V operation/Duty level: CMOS**

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -20$ to $+80^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	2.0	4.0	ns
	t_{r4}		$C_L = 30pF$	–	3.0	6.0	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	2.0	4.0	ns
	t_{f4}		$C_L = 30pF$	–	3.0	6.0	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 30MHz$	45	–	55	%	
Output disable delay time ²	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time ²	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

5V operation/Duty level: CMOS

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	1.5	3.0	ns
	t_{r2}		$C_L = 50pF$	–	4.0	8.0	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	1.5	3.0	ns
	t_{f2}		$C_L = 50pF$	–	4.0	8.0	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 50pF$, $f = 30MHz$	40	–	60	%	
Output disable delay time ²	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time ²	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

SM5010 series

5010EA× series

3V operation/Duty level: CMOS

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.1V_{DD}$ to $0.9V_{DD}$	–	8	16	ns
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.9V_{DD}$ to $0.1V_{DD}$	–	8	16	ns
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 30MHz$	40	–	60	%
Output disable delay time ²	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns
Output enable delay time ²	t_{PZL}		–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.
2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

5V operation/Duty level: CMOS

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	5	10	ns
	t_{r2}		$C_L = 50pF$	–	13	26	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	5	10	ns
	t_{f2}		$C_L = 50pF$	–	13	26	
Output duty cycle ¹	Duty1	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	$f = 30MHz$	45	–	55	%
	Duty2		$f = 40MHz$	40	–	60	
Output disable delay time ²	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time ²	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.
2. Oscillator stop function is built-in. When INHN goes LOW, normal output stops. When INHN goes HIGH, normal output is not resumed until after the oscillator start-up time has elapsed.

SM5010 series

5010FN× series

3V operation/Duty level: CMOS

$V_{DD} = 2.7$ to $3.6V$, $V_{SS} = 0V$, $T_a = -10$ to $+70^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit
			min	typ	max	
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.1V_{DD}$ to $0.9V_{DD}$	–	3.0	6.0	ns
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $C_L = 15pF$, $0.9V_{DD}$ to $0.1V_{DD}$	–	3.0	6.0	ns
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 40MHz$	40	–	60	%
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 3.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns
Output enable delay time	t_{PZL}		–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

5V operation/Duty level: CMOS

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$

$30 \leq f \leq 50MHz$: $T_a = -20$ to $+80^\circ C$, $50 < f \leq 70MHz$: $T_a = -15$ to $+75^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	1.5	3.0	ns
	t_{r2}		$C_L = 50pF$	–	3.0	6.0	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	1.5	3.0	ns
	t_{f2}		$C_L = 50pF$	–	3.0	6.0	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$	$C_L = 50pF$ $f = 50MHz$	45	–	55	%
			$C_L = 15pF$ $f = 70MHz$	40	–	60	
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

SM5010 series

5010FH× series

5V operation/Duty level: CMOS

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$

$30 \leq f \leq 50MHz$: $T_a = -20$ to $+80^\circ C$, $50 < f \leq 60MHz$: $T_a = -15$ to $+75^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	4	8	ns
	t_{r2}		$C_L = 50pF$	–	11	21	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	4	8	ns
	t_{f2}		$C_L = 50pF$	–	11	21	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	$f = 50MHz$	45	–	55	%
			$f = 60MHz$	40	–	60	
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time	t_{PZL}			–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

5010HN× series

5V operation/Duty level: CMOS

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r1}	Measurement cct 6, load cct 1, $0.1V_{DD}$ to $0.9V_{DD}$	$C_L = 15pF$	–	1.5	3.0	ns
	t_{r2}		$C_L = 50pF$	–	3.0	6.0	
Output fall time	t_{f1}	Measurement cct 6, load cct 1, $0.9V_{DD}$ to $0.1V_{DD}$	$C_L = 15pF$	–	1.5	3.0	ns
	t_{f2}		$C_L = 50pF$	–	3.0	6.0	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 50pF$, $f = 50MHz$		45	–	55	%
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 1, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$		–	–	100	ns
Output enable delay time	t_{PZL}			–	–	100	ns

1. The duty cycle characteristic is checked the sample chips of each production lot.

5010HK× series

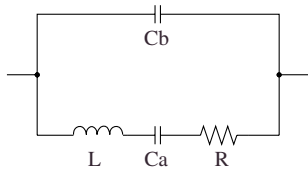
5V operation/Duty level: TTL

$V_{DD} = 4.5$ to $5.5V$, $V_{SS} = 0V$, $T_a = -40$ to $+85^\circ C$ unless otherwise noted.

Parameter	Symbol	Condition	Rating			Unit	
			min	typ	max		
Output rise time	t_{r3}	Measurement cct 6, load cct 2, 0.4V to 2.4V	$C_L = 15pF$	–	1.2	2.4	ns
	t_{r5}		$C_L = 50pF$	–	2.0	5.0	
Output fall time	t_{f3}	Measurement cct 6, load cct 2, 2.4V to 0.4V	$C_L = 15pF$	–	1.2	2.4	ns
	t_{f5}		$C_L = 50pF$	–	2.0	5.0	
Output duty cycle ¹	Duty	Measurement cct 6, load cct 2, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$, $f = 50MHz$	45	–	55	%	
Output disable delay time	t_{PLZ}	Measurement cct 7, load cct 2, $V_{DD} = 5.0V$, $T_a = 25^\circ C$, $C_L = 15pF$	–	–	100	ns	
Output enable delay time	t_{PZL}		–	–	100	ns	

1. The duty cycle characteristic is checked the sample chips of each production lot.

Current consumption and Output waveform with NPC's standard crystal



for Fundamental oscillator

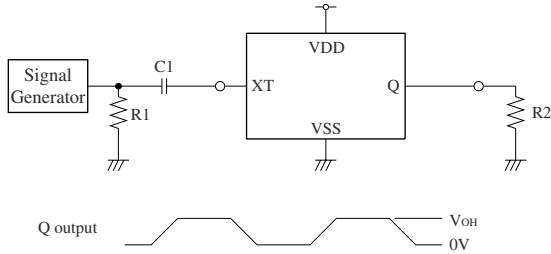
f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
30	17.2	4.36	6.46	2.26
40	16.8	2.90	5.47	2.08

for 3rd overtone oscillator

f [MHz]	R [Ω]	L [mH]	Ca [fF]	Cb [pF]
30	18.62	16.24	1.733	5.337
40	20.53	11.34	1.396	3.989
50	22.17	7.40	1.370	4.105
60	15.37	3.83	1.836	5.191
70	25.42	4.18	1.254	5.170

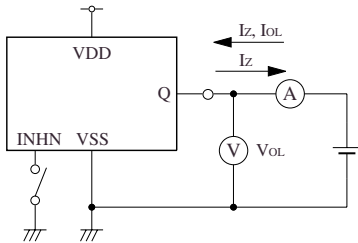
MEASUREMENT CIRCUITS

Measurement cct 1

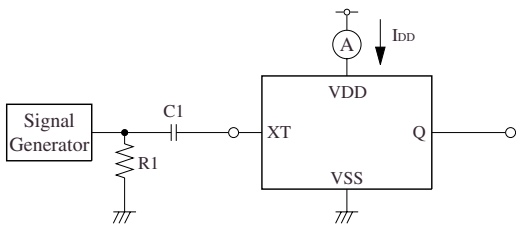


- 2.0V_{P-P}, 10MHz sine wave input signal (3V operation)
 3.5V_{P-P}, 10MHz sine wave input signal (5V operation)
 C1 : 0.001μF
 R1 : 50Ω
 R2 : 5010AN×, BN×, DN×, AK×, BK×
 3V operation: 263Ω
 5V operation: 245Ω
 5010FN×, HN×, HK×
 3V operation: 275Ω
 5V operation: 245Ω
 5010CL×
 3V operation: 275Ω
 5V operation: 250Ω
 5010EA×, AH×, BH×
 3V operation: 1050Ω
 5010EA×, AH×, BH×, FH×
 5V operation: 975Ω

Measurement cct 2

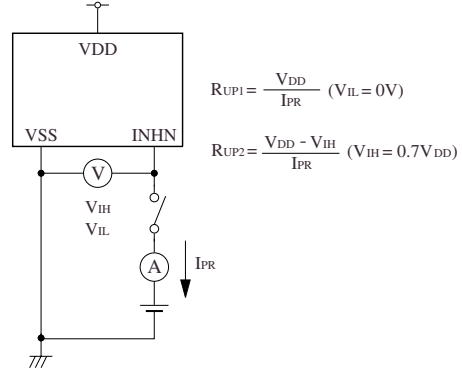


Measurement cct 3

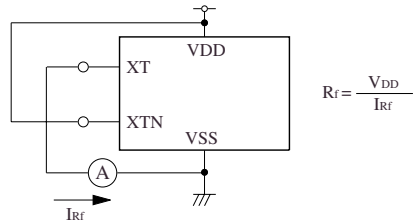


- 2.0V_{P-P}, 30MHz sine wave input signal (3V operation)
 3.5V_{P-P}, 30MHz sine wave input signal (5V operation)
 C1 : 0.001μF
 R1 : 50Ω

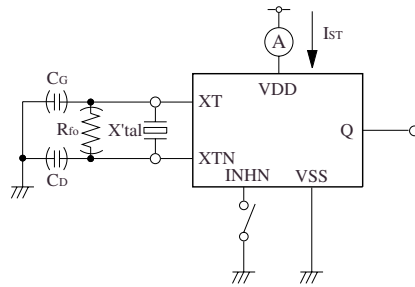
Measurement cct 4



Measurement cct 5

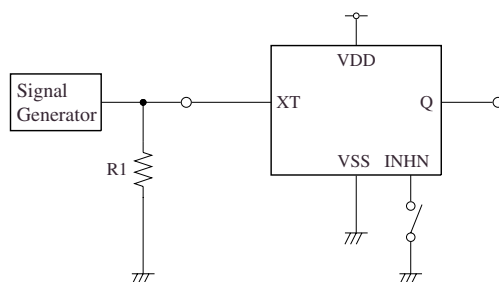


Measurement cct 6



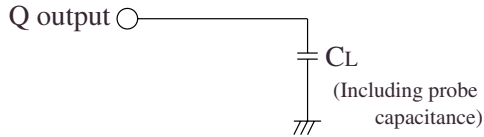
- Crystal oscillation
 C_G, C_D: 22pF (5010DN×)
 R_{f0}: 3.0kΩ (5010H××)

Measurement cct 7



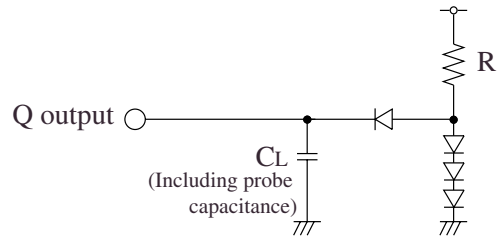
- R1 : 50Ω

Load cct 1



$C_L = 15\text{pF}$: DUTY, I_{DD} , t_{r1} , t_{f1}
 $C_L = 30\text{pF}$: t_{r4} , t_{f4}
 $C_L = 50\text{pF}$: t_{r2} , t_{f2}

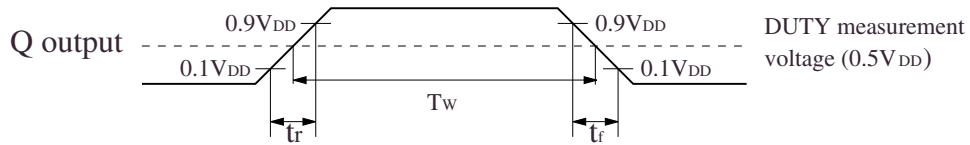
Load cct 2



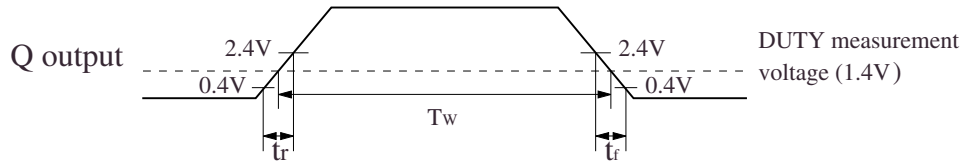
$C_L = 15\text{pF}$: DUTY, I_{DD} , t_{r3} , t_{f3}
 $C_L = 50\text{pF}$: t_{r5} , t_{f5}
 $R = 400\Omega$

Switching Time Measurement Waveform

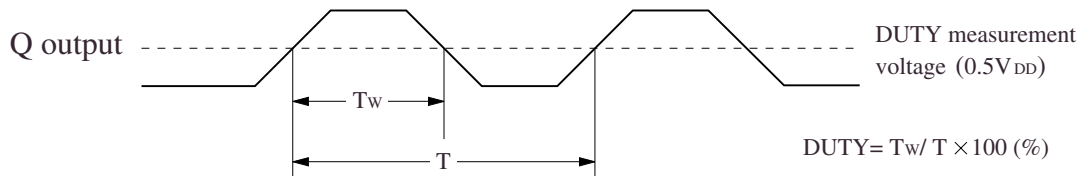
Output duty level (CMOS)



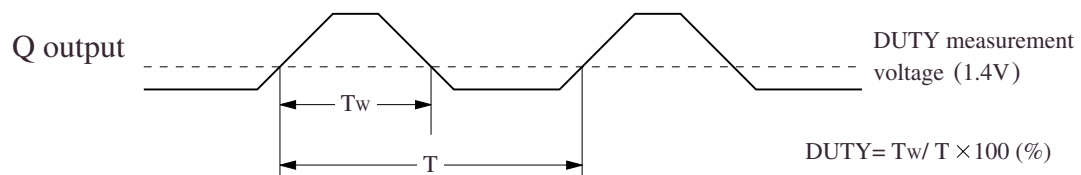
Output duty level (TTL)

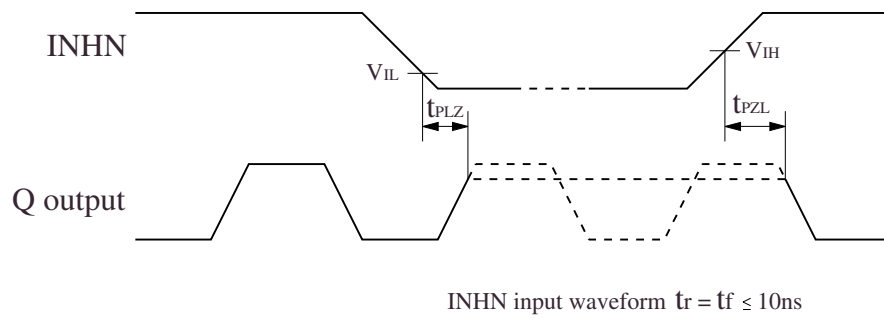


Output duty cycle (CMOS)



Output duty cycle (TTL)



Output Enable/Disable Delay

Note (CL×/EA× series only): when the device is in standby, the oscillator stops. When standby is released, the oscillator starts and stable oscillator output occurs after a short delay.

Please pay your attention to the following points at time of using the products shown in this document.

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The logo for SEIKO NPC CORPORATION, consisting of the letters 'NPC' in a bold, black, sans-serif font.

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